



# BAV99S

**VOLTAGE** 85 Volts **CURRENT** 200 mA

**SOT-363** Unit: inch ( mm )

## HIGH SPEED SWITCHING DIODE ARRAY

This device comes with two pairs of high speed switching diodes connected in series, where both pairs are electrically isolated, offering a very low capacitance, minimizing the insertion losses in data transmission lines.

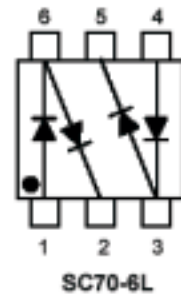
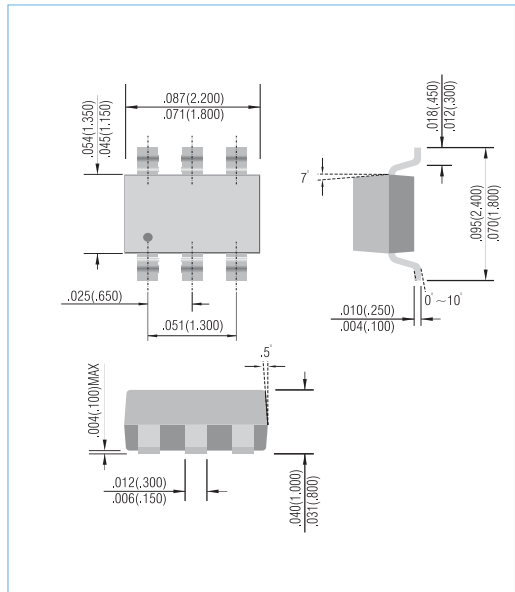
### FEATURES

- Maximum capacitance of 1.5pF
- Maximum leakage current of 2.5  $\mu$ A
- Reverse breakdown voltage of 70V
- Rail to rail ESD protection
- Overshoot and undershoot switching control
- Mobile phones and accessories
- Video game consoles connector ports
- Pb free product are available : 99% Sn above can meet Rohs environment substance directive request

### MECHANICAL DATA

Case: SOT-363 molded plastic

Terminals: Lead solderable per MIL-STD-202G, Method 208.



### MAXIMUM RATINGS (PER DIODE) $T_J=25^{\circ}\text{C}$ , UNLESS OTHERWISE NOTED

Rating	Symbol	Value	Units
Maximum repetitive peak reverse voltage	$V_{RRM}$	85	V
Continuous reverse voltage	$V_R$	75	V
Continuous forward voltage	$I_F$	200	mA
Non-repetitive peak forward current, $t=1 \mu$ sec, $T_J=25^{\circ}\text{C}$ square wave	$I_{FSM}$	4.5	A
Total power dissipation, $T_J=85^{\circ}\text{C}$	$P_{TOT}$	250	mW
Operating Junction Temperature range	$T_J$	-50 to + 150	$^{\circ}\text{C}$
Storage temperature range	$T_{STG}$	-50 to + 150	$^{\circ}\text{C}$
Soldering Temperature, $t_{max} = 10$ secs	$T_L$	260	$^{\circ}\text{C}$



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## ELECTRICAL CHARACTERISTICS (PER DIODE) $T_J=25^{\circ}\text{C}$ , UNLESS OTHERWISE NOTED

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Breakdown voltage	$V_{BR}$	$I_{BR}=100\ \mu\text{A}$	75			
Forward voltage	$V_F$	$I_F=1\text{mA}$			715	mV
		$I_F=10\text{mA}$			855	mV
		$I_F=50\text{mA}$			1	V
		$I_F=150\text{mA}$			1.25	V
Reverse leakage current	$I_R$	$V_R=75\text{V}$			2.5	$\mu\text{A}$
Reverse leakage current at $T_J=150^{\circ}\text{C}$	$I_R$	$V_R=25\text{V}$			30	$\mu\text{A}$
		$V_R=70\text{V}$			50	$\mu\text{A}$
Junction capacitance	$C_D$	0Vdc Bias, $f=1\text{MHz}$			1.5	pF
Reverse recovery time	$t_{rr}$	$I_F=10\text{mA}, I_R=10\text{mA}$ $R_L=100\ \text{Ohms}$ measured at $I_R=1\text{mA}$			4	ns
Forward recovery voltage	$V_{FR}$	$I_F=10\text{mA}, t_r=20\text{nsec}$			1.75	V



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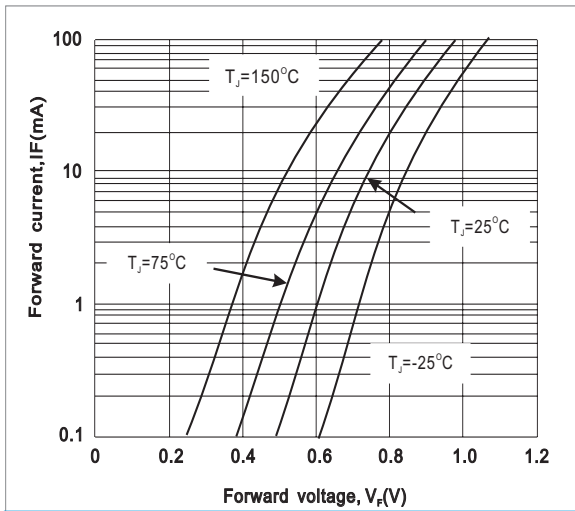


Fig.1-Typical forward voltage

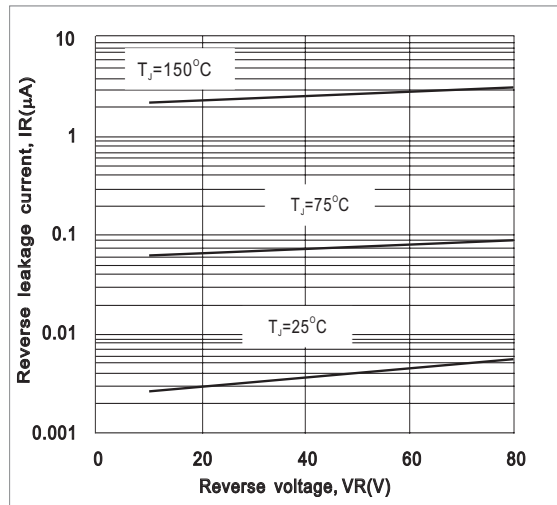


Fig.2-Typical reverse leakage

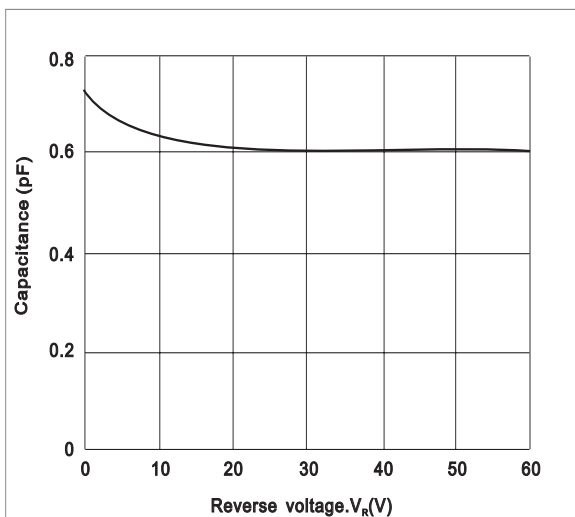


Fig.3-Typical capacitance